

## CIR-S4DUSW2116G

DDR4 DIMM 2133MHz 16GB

### Description

CIR-S4DUSW2116G is a CMOS Double Data Rate IV (DDR4) Synchronous DRAM module, in Fine Ball Grid Array (FBGA) packages on a 288pin glass-epoxy substrate.

DDR4 unbuffered UDIMM series offers fully synchronous operations referenced to both rising and falling edges of the clock. The data paths are internally pipelined and 8-bit prefetched to achieve very high bandwidth.

### Specifications

Density	16GB
Pin Count	288pin
Type	Unbuffered
Dimensions	133.35mm x 31.25mm
ECC	Non-ECC
Component Config	1G x 8 bit
Data Rate	2133 MHz
CAS Latency	15
Voltage	1.2V
PCB Layers	8
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Dual Rank

### Features

- JEDEC standard
- VDD=VDDQ = 1.2V±0.06V (1.14V~1.26V)
- Programmable CAS Latency(posted CAS): 11,12,13,14,15
- 8-bit pre-fetch
- 16 Banks (4 Bank Groups)
- Internal(self) calibration : Internal self calibration through ZQ pin
- On Die Termination using ODT pin
- Average Refresh Period
  - 7.8us ( TCASE ≤ 85°C )
  - 3.9us (85°C < TCASE < 95°C)
- Asynchronous Reset pin supported
- Burst Length: 8 or BC4
- POD (Pseudo Open Drain) interface for data input/output
- Serial presence detect (SPD)
- All of products are Halogen-free
- All of Lead-Free products are compliant for RoHS

